

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A stack-type semiconductor device formed by stacking a plurality of semiconductor devices, at least an undermost semiconductor device among the plurality of semiconductor devices comprising:

a semiconductor element having ~~a first through hole~~ ~~holes formed therein~~ and a plurality of electrodes formed on a first surface of the semiconductor ~~element; element, each of the electrodes having second through holes formed therein, the second through holes respectively connecting with the first through holes, the second through holes having inner wall surfaces;~~

~~an insulating film formed on a region including the inner wall surfaces of the second through holes, the insulating film having third through holes inside the second through holes, respectively;~~

a conductive layer which is electrically connected to the electrodes, and is provided from the first surface through ~~an inner wall-walls~~ of the ~~first through hole-holes~~ to a second surface of the semiconductor ~~element- element,~~ which is opposite to the first surface; and

a plurality of connecting portions provided on the conductive layer so that a distance between two connecting portions among the plurality of connecting portions is different from a distance between at least two electrodes among the plurality of electrodes, on at least one of the first and second surfaces.

2. (Currently Amended) A stack-type semiconductor device formed by stacking a plurality of the semiconductor devices adjacent ~~semiconductor devices~~, ~~among the~~

~~plurality of the semiconductor devices being electrically connected by the conductive layer, each of the semiconductor device devices comprising:~~

a semiconductor element having a first through hole holes formed therein and a plurality of electrodes formed on a first surface of the semiconductor element; element, each of the electrodes having second through holes formed therein, the second through holes respectively connecting with the first through holes, the second through holes having inner wall surfaces;

an insulating film formed on a region including the inner wall surfaces of the second through holes, the insulating film having third through holes inside the second through holes, respectively;

a conductive layer which is electrically connected to the electrodes, and is provided from the first surface through an inner wall-walls of the first through hole-holes to a second surface of the semiconductor element which is opposite to the first surface; and

a plurality of connecting portions provided on the conductive layer so that a distance between two connecting portions among the plurality of connecting portions is different from a distance between at least two electrodes among the plurality of electrodes, on at least one of the first and second surfaces-surfaces,

wherein adjacent semiconductor devices are electrically connected by the conductive layer to the plurality of the semiconductor devices.

3. (Canceled)

4. (Canceled)

5. (Currently Amended) The stack-type semiconductor device as defined in claim 1,

wherein an-the undermost semiconductor device is arranged so that the first surface of the semiconductor element faces other stacked semiconductor devices.